

## **Description**

The AON6358 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = 30V I_{D} = 150A$ 

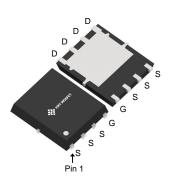
 $R_{DS(ON)} < 2.4 \text{m}\Omega \text{ V}_{GS} = 10 \text{V}$ 

## **Application**

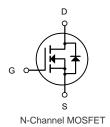
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L (DFN-8(5.1x5.8))



## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
AON6358	DFN5X6-8L(DFN-8(5.1x5.8))	HXY MOSFET	5000

## Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter Rating		Units		
Vos	Drain-Source Voltage	ource Voltage 30			
Vgs	Gate-Source Voltage	±20	V		
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	150	А		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	80	Α		
Іом	Pulsed Drain Current <sup>2</sup>	160	А		
EAS	Single Pulse Avalanche Energy <sup>3</sup>	180	mJ		
las	Avalanche Current	60	Α		
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	187	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W		
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	1.1	°C/W		



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			٧	
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.014		V/°C	
D	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =30A	2		2.4	m()	
R <sub>DS(ON)</sub>	Static Dialii-Source On-Resistance	V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		2.5	3.2	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	\/\/	1.2		2.5	V	
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=250uA$		-4		mV/°C	
l	Drain Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uA	
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA	
Igss	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	orward Transconductance V <sub>DS</sub> =5V , I <sub>D</sub> =30A		50		S	
Rg	Gate Resistance	sate Resistance V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.7		Ω	
Qg	Total Gate Charge (4.5V)			56.9			
Q <sub>gs</sub>	Gate-Source Charge V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =15A			13.8		nC	
Q <sub>gd</sub>	Gate-Drain Charge			23.5			
T <sub>d(on)</sub>	Turn-On Delay Time			20.1			
Tr	Rise Time	$V_{DD}$ =15V , $V_{GS}$ =10V , $R_{G}$ =3.3 $\Omega$ ,		6.3		no	
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =1A		124.6		ns	
T <sub>f</sub>	Fall Time			15.8			
Ciss	Input Capacitance			4345			
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		340		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			225			

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			150	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V

### Note:

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V, $V_{GS}$ =10V,L=0.1mH, $I_{AS}$ =60A
- 4. The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.
- 6. Package limitation current is 85A.

## **Typical Characteristics**

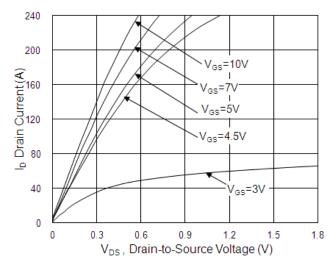


Fig.1 Typical Output Characteristics

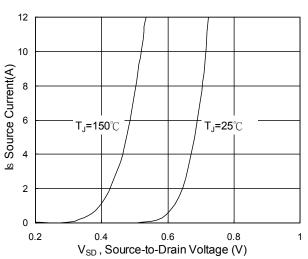


Fig.3 Forward Characteristics of Reverse

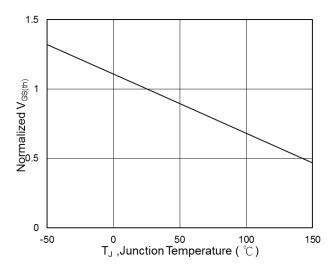


Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$ 

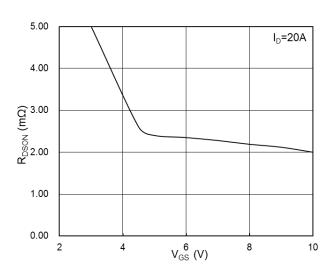


Fig.2 On-Resistance v.s Gate-Source

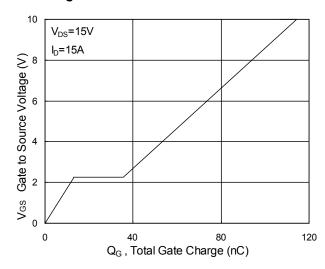


Fig.4 Gate-Charge Characteristics

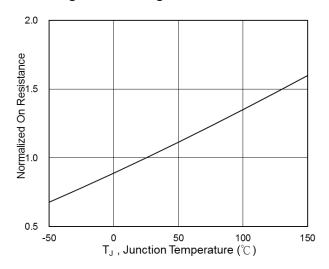
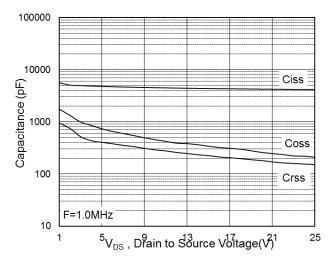


Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>



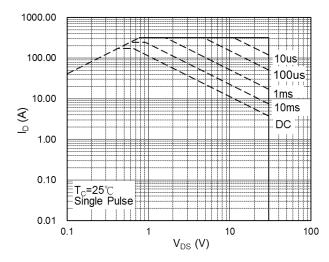


Fig.7 Capacitance

Fig.8 Safe Operating Area

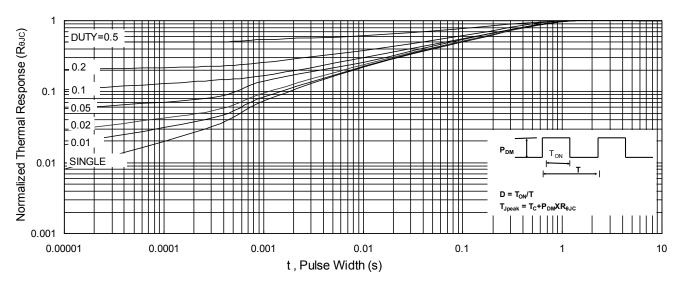


Fig.9 Normalized Maximum Transient Thermal Impedance

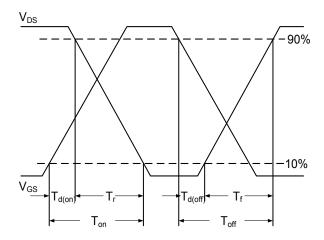


Fig.10 Switching Time Waveform

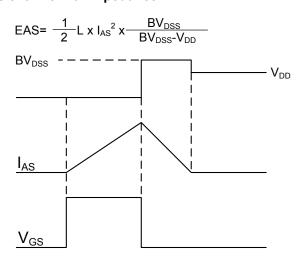
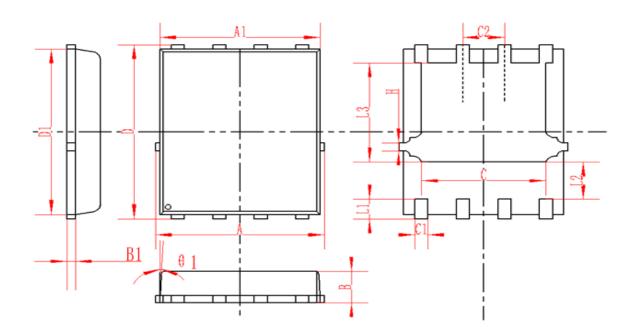


Fig.11 Unclamped Inductive Switching Waveform



# DFN5X6-8L(DFN-8(5.1x5.8)) Package Information



SYMBOL		MM			INCH	
STIVIDOL	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1		0.254REF		0.010REF		
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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